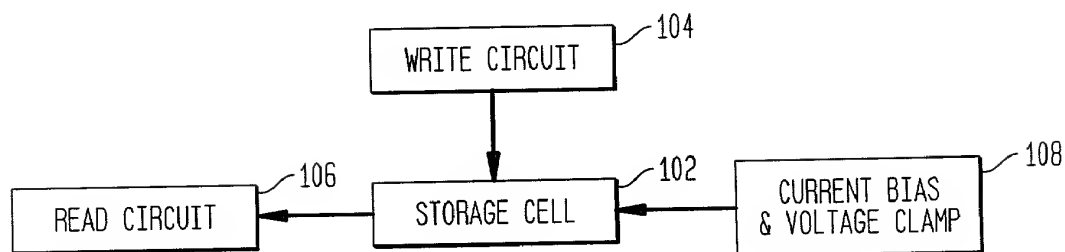
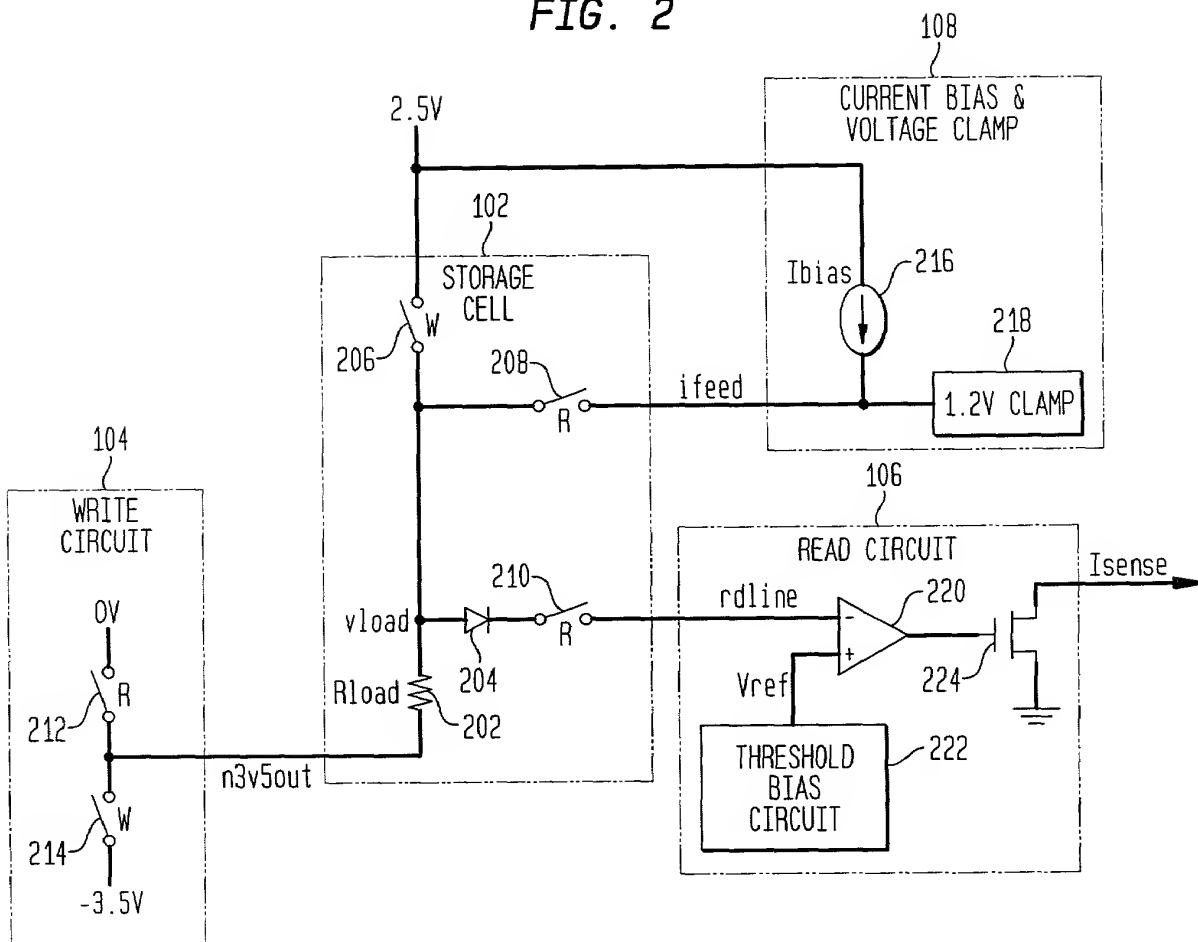


FIG. 1



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FIG. 2



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FIG. 3

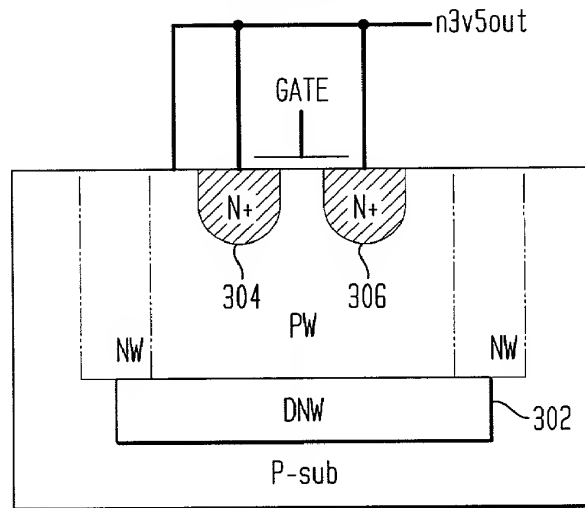
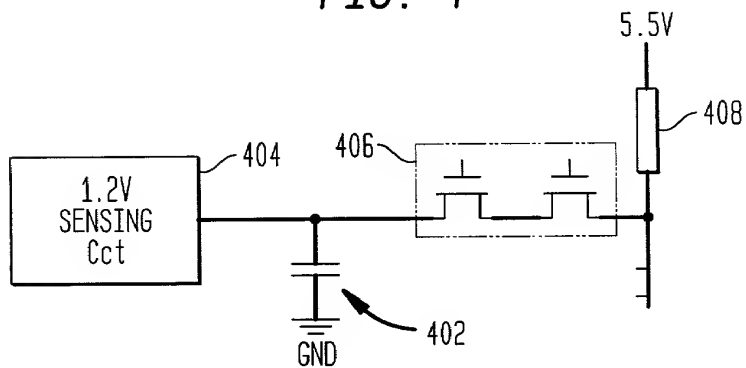


FIG. 4



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FIG. 5A

NMOS FET $10 \times 10 \text{ } \mu\text{m}^2$ S/D FLOAT

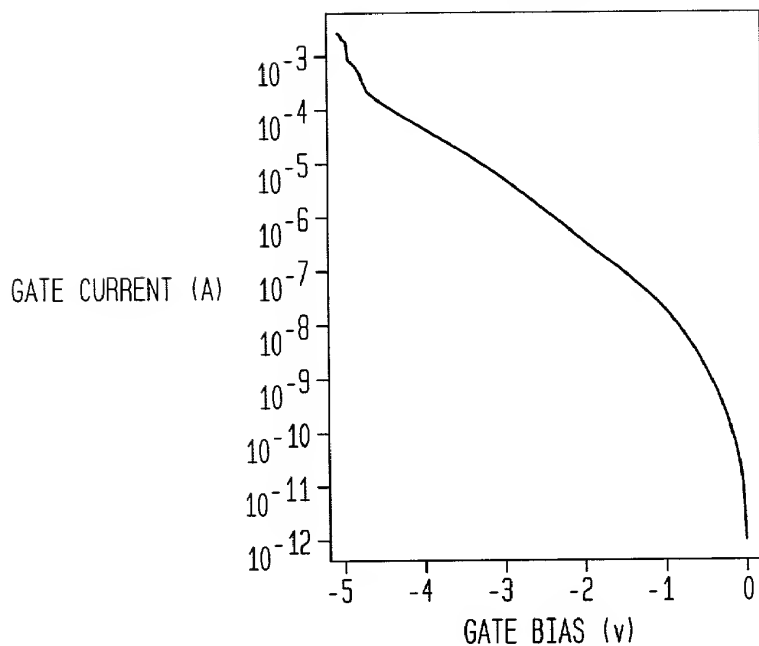
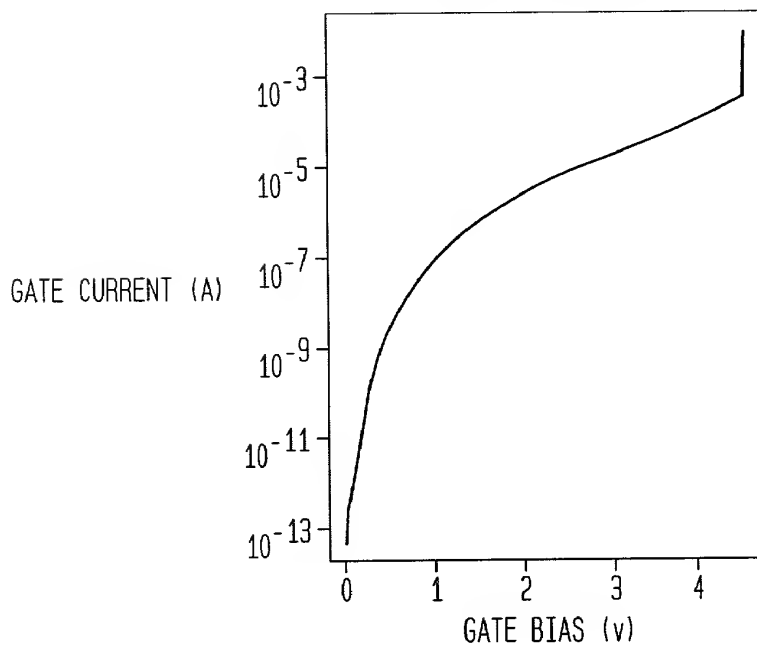


FIG. 5B

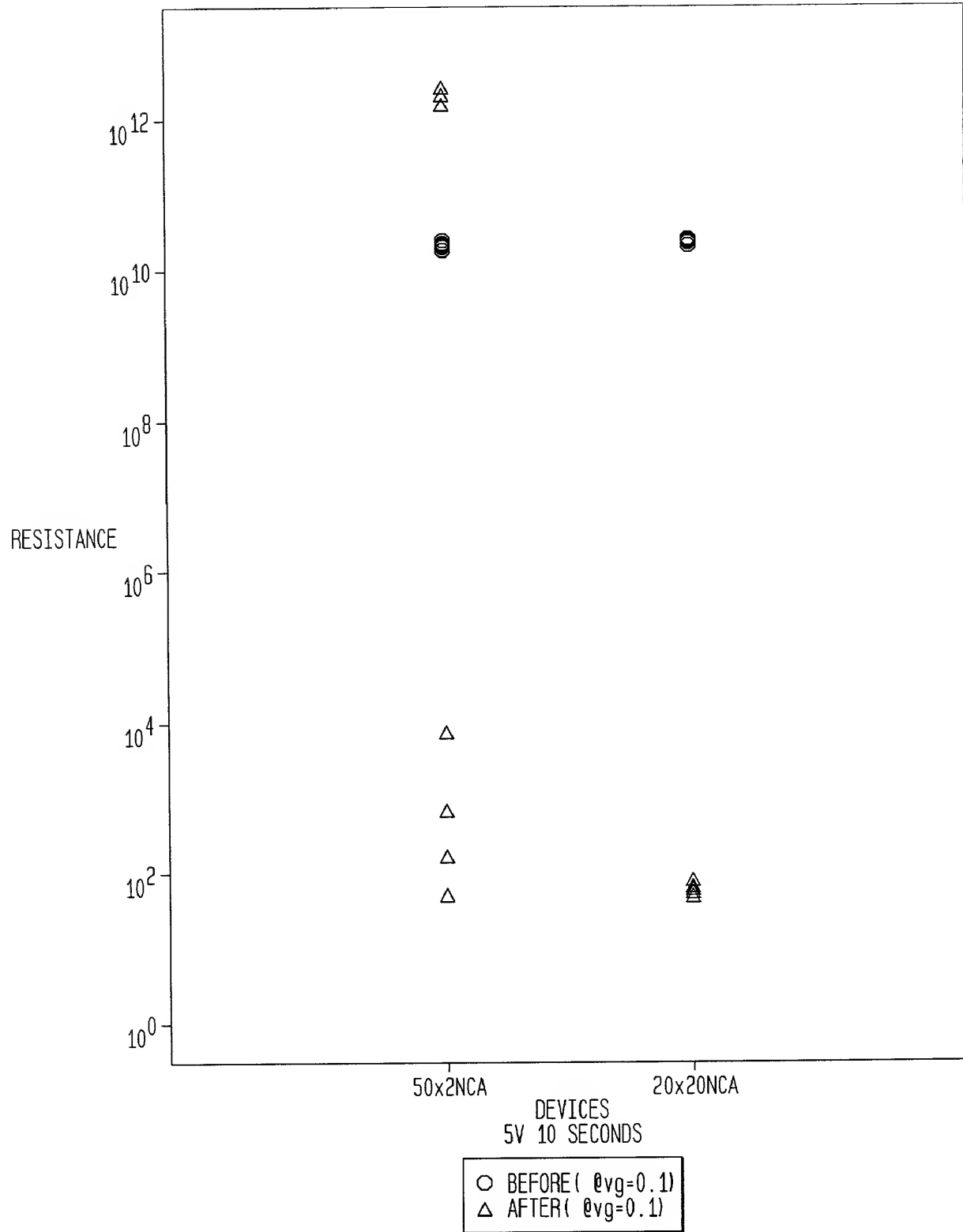
NMOS FET $10 \times 10 \text{ } \mu\text{m}^2$



Appl No. 09/739,752, Group Art Unit: 2811
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 Through Direct-Tunneling Oxide Breakdown

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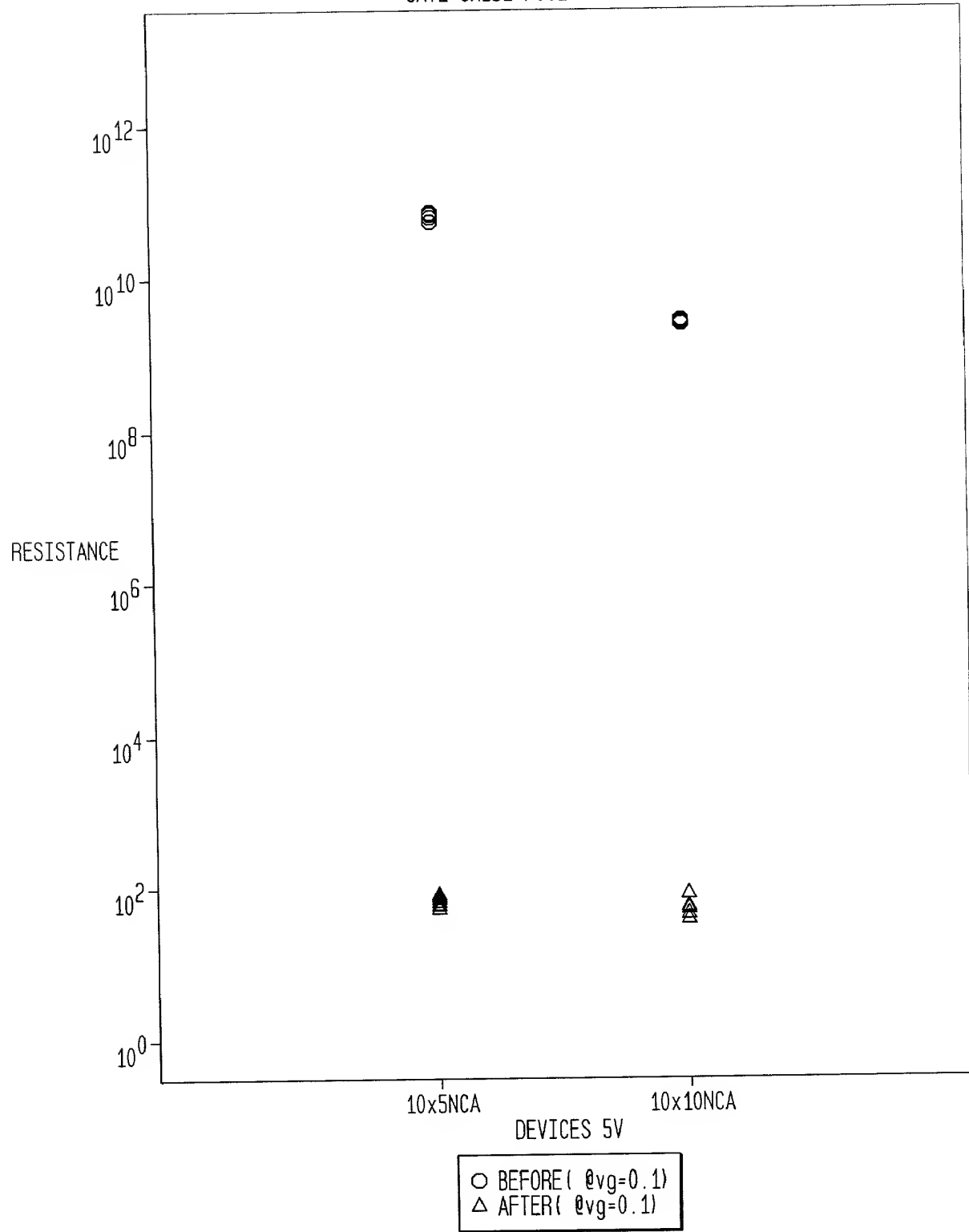
FIG. 6A
 GATE OXIDE FUSE



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FIG. 6B

GATE OXIDE FUSE



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FIG. 7

